



Product Overview

2N5302: High Power NPN Bipolar Power Transistor

For complete documentation, see the data sheet

Product Description

The High Power Bipolar NPN Transistor is designed for use in power amplifier and switching circuits applications.

Features

- Low Collector-Emitter Saturation Voltage
 $V_{CE(sat)}=0.75$ Vdc (Max) @ IC = 10 Adc
- Pb-Free Package is Available

Part Electrical Specifications

Product	Compliance	Status	Polarity	IC Continuous (A)	V(BR)CEO Min (V)	hFE Min	hFE Max	fT Min (MHz)	PTM Max (W)	Package Type
2N5302G	Pb-free	Active	NPN	30	60	15	60	2	200	TO-204-2

For more information please contact your local sales support at www.onsemi.com

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